NSN 5961-01-089-8862

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Inclosure Material:

Metal

Overall Length:

Between 0.250 inches and 0.450 inches

Overall Diameter:

0.875 inches

Mounting Facility Quantity:

2

Internal Configuration:

Junction contact

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-3

Electrode Internally-electrically Connected To Case:

Collector

Mounting Method:

Unthreaded hole

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

80.0 breakdown voltage, collector-to-base, emitter open and 50.0 breakdown voltage, collector-to-emitter, base open and 6.0 breakdown voltage, emitter-to-base, collector open

Current Rating Per Characteristic:

500.00 milliamperes source cutoff current

Power Rating Per Characteristic:

800.0 milliwatts small-signal input power, common-collector

Maximum Operating Tempurature Per Measurement Point:

175.0 degrees celsius junction

Special Features:

Junction pattern arrangement: npn

Terminal Type And Quantity:

1 case and 2 pin

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

Fiig:

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